

MJE13002G5 (3DD13002G5)

硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

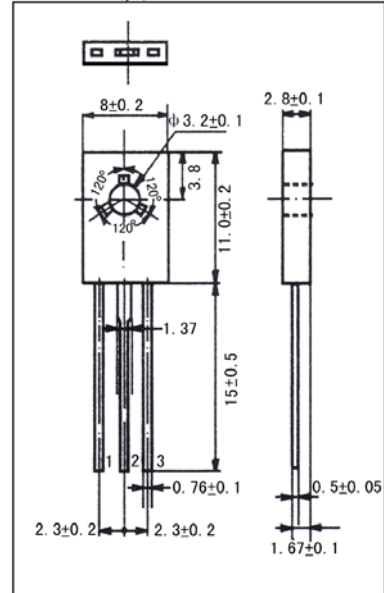
用途：主要用于节能灯、日光灯电子镇流器及其它开关、振荡电路。

Purpose: High frequency electronic lighting ballast applications, converters, inverters, switching regulators, etc.

极限参数/Absolute maximum ratings(Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V <sub>CB0</sub>	600	V
V <sub>CE0</sub>	400	V
V <sub>EB0</sub>	9.0	V
I <sub>C</sub>	0.75	A
P <sub>C</sub> (Ta=25°C)	1.25	W
P <sub>C</sub> (T <sub>c</sub> =25°C)	30	W
T <sub>j</sub>	150	°C
T <sub>stg</sub>	-55~150	°C

T0-126反 单位 :mm



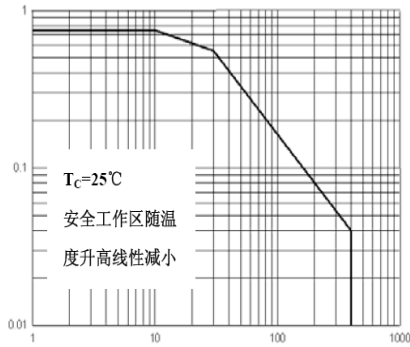
引脚：1.B 2.C 3.E

电性能参数/Electrical characteristics(Ta=25°C)

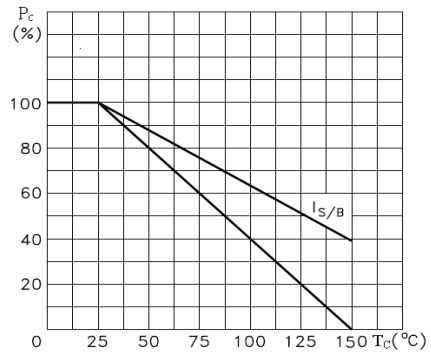
参数符号 Symbol	测试条件 Test condition		数值 Rating			单位 Unit
			最小值 Min	典型值 Typ	最大值 Max	
V <sub>CB0</sub>	I <sub>C</sub> =1mA	I <sub>E</sub> =0	600			V
V <sub>CE0</sub>	I <sub>C</sub> =10mA	I <sub>B</sub> =0	400			V
V <sub>EB0</sub>	I <sub>E</sub> =1mA	I <sub>C</sub> =0	9.0			V
I <sub>CB0</sub>	V <sub>CB</sub> =600V	I <sub>E</sub> =0			0.1	mA
I <sub>CE0</sub>	V <sub>CE</sub> =400V	I <sub>B</sub> =0			0.1	mA
I <sub>EB0</sub>	V <sub>EB</sub> =9.0V	I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	V <sub>CE</sub> =5.0V	I <sub>C</sub> =200mA	10		40	
V <sub>CE(sat)</sub>	I <sub>C</sub> =300mA	I <sub>B</sub> =60mA			0.5	V
V <sub>BE(sat)</sub>	I <sub>C</sub> =300mA	I <sub>B</sub> =60mA			1.2	V
f <sub>T</sub>	V <sub>CE</sub> =10V I <sub>C</sub> =100mA	f=1.0MHz	5.0			MHz
t <sub>f</sub>	V <sub>CE</sub> =5V	I <sub>C</sub> =100mA			0.6	μs
t <sub>S</sub>	(UI9600)				3.5	μs

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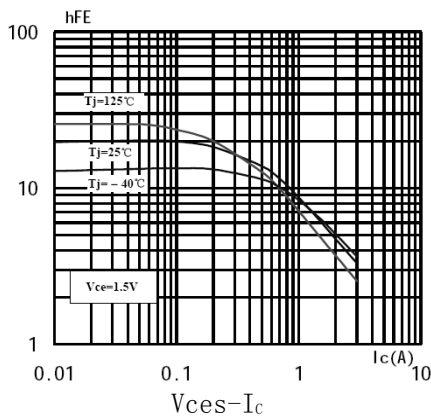
SOA (DC)



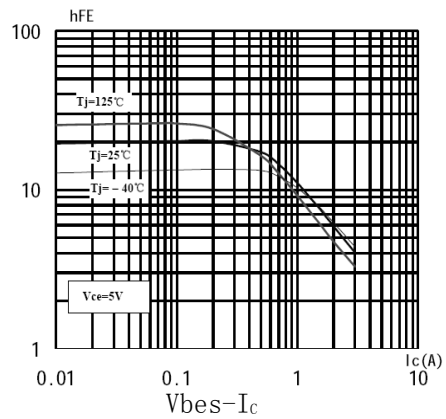
$P_C - T_C$



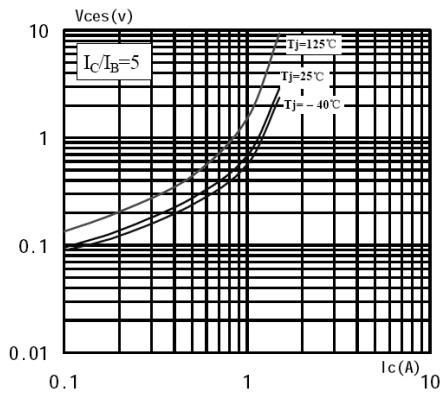
$h_{FE} - I_C$



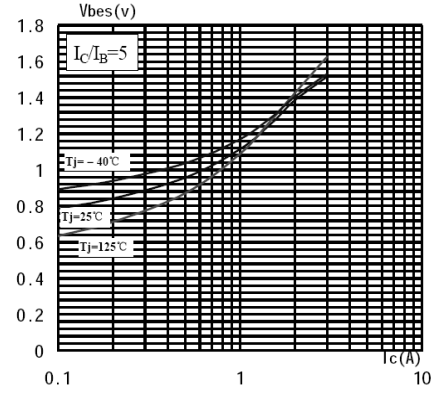
$h_{FE} - I_C$



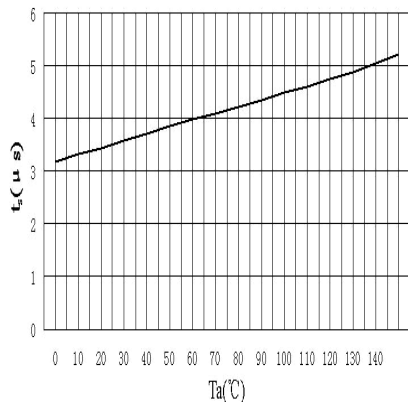
$V_{CES} - I_C$



$V_{BES} - I_C$



$t_s - T_a$



$h_{FE} - T_a$

